

6- Ω , Low Voltage, Dual SPST Analog Switch

DESCRIPTION

The DG2737, DG2738 and DG2739 are high performance, low on-resistance analog switches of dual SPST configuration.

Built on Vishay Siliconix's sub-micro CMOS technology, the DG2737, DG2738, DG2739 achieve switch on-resistance of 6 Ω at 3 V V+. Its -3 dB bandwidth is typically 720 MHz.

It can switch signals with amplitudes of up to V_{CC} to be transmitted in either direction.

Combining low power, high speed, low on-resistance and small physical size, the DG2737, DG2738, DG2739 are ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2737, DG2738, DG2739 come in a small miniQFN-8 lead package (1.4 x 1.4 x 0.55 mm). As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations and is 100 % RoHS compliant.

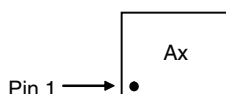
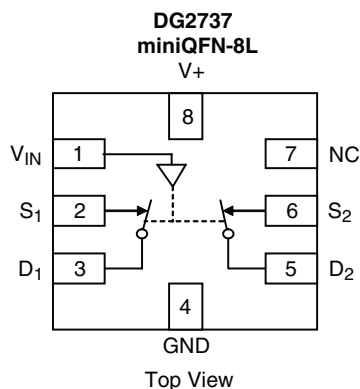
FEATURES

- Voltage range: 2.3 V to 4.3 V
- Low on-resistance: 6 Ω typ. at 3 V
- -48 dB crosstalk at 240 MHz
- Low power consumption
- Ultra small miniQFN8 package of 1.4 x 1.4 x 0.55 mm
- > 300 mA latch up current per JEDEC78
- Switch exceeds 5 kV ESD/HBM

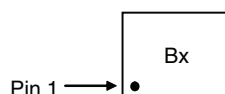
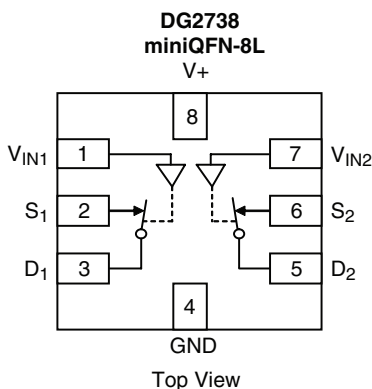


RoHS
COMPLIANT

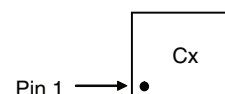
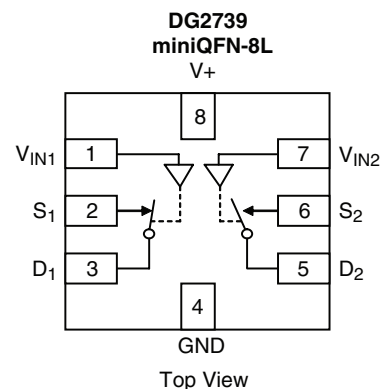
FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: Ax for DG2737
x = Date/Lot Traceability Code



Device Marking: Bx for DG2738
x = Date/Lot Traceability Code



Device Marking: Cx for DG2739
x = Date/Lot Traceability Code

TRUTH TABLE 1

Input	Logic	DG2737	
		S ₁ and D ₁	S ₂ and D ₂
V _{IN}	Low	ON	ON
	High	OFF	OFF

TRUTH TABLE 2

Input	Logic	DG2738		DG2739	
		S ₁ and D ₁	S ₂ and D ₂	S ₁ and D ₁	S ₂ and D ₂
V _{IN1}	Low	ON	X	ON	X
	High	OFF	X	OFF	X
V _{IN2}	Low	X	ON	X	OFF
	High	X	OFF	X	ON

ORDERING INFORMATION

Temp. Range	Package	Part Number
- 40 °C to 85°C	miniQFN-8L	DG2737DN-T1-E4 DG2738DN-T1-E4 DG2739DN-T1-E4

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Limit	Unit
Reference to GND	V ₊	V
	V _{IN} , D, S ^a	
Current (Any terminal except D or S)	30	mA
Continuous Current (D or S)	± 300	
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)	± 500	
Storage Temperature (D Suffix)	- 65 to 150	°C
Power Dissipation (Packages) ^b	miniQFN-8L ^c	mW

Notes:

a. Signals on V_{IN}, D, or S exceeding V₊ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 2.4 mW/°C above 70 °C.

SPECIFICATIONS V₊ = 3 V

Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 3 V, V _{IN} = 0.4 V or 1.4 V ^e	Temp. ^a	Limits - 40 °C to 85 °C			Unit
				Min. ^b	Typ. ^c	Max. ^b	
Analog Switch							
Analog Signal Range ^d	V _{analog}	R _{ON}	Full	0		V+	V
On-Resistance	R _{ON}	V+ = 3 V, I _S = 8 mA, V _D = 0.4 V	Room		6	8	Ω
			Full			9	
R _{ON} Match ^d	ΔR _{ON}	V+ = 3 V, I _S = 8 mA, V _D = 0.4 V	Room		0.1	0.5	
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 3 V, I _S = 8 mA, V _D = 0 V, 1 V	Room		2.6	4	



SPECIFICATIONS V+ = 3 V								
Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 3 V, VIN = 0.4 V or 1.4 V ^e	Temp. ^a	Limits - 40 °C to 85 °C			Unit	
				Min. ^b	Typ. ^c	Max. ^b		
Analog Switch								
Switch Off Leakage Current	IS(off)	V+ = 4.3 V, VS = 0.3 V/3.3 V, VD = 3.3 V/0.3 V	Room	- 10		10	nA	
			Full	- 100		100		
	ID(off)		Room	- 10		10		
			Full	- 100		100		
Channel-On Leakage Current	ID(on)	V+ = 4.3 V, VS = VD = 4 V/0.3 V	Room	- 10		10		
			Full	- 100		100		
Digital Control								
Input High Voltage	VINH	V+ = 2.3 V to 4.3 V	Full	1.3			V	
Input Low Voltage	VINL		Full			0.5		
Input Current	IINL or IINH	VIN = 0 or V+	Full	- 1		1	μA	
Dynamic Characteristics								
Turn-On Time ^e	tON	V+ = 2.3 V to 3.6 V, VNO or VS = 1.5 V, RL = 50 Ω, CL = 35 pF	Room		23	60	ns	
			Full			70		
Turn-Off Time ^e	tOFF		Room		13	50		
			Full			60		
Break-Before-Make Time	tBBM		V+ = 2.3 V to 4.3 V	Room		6		ns
				Full	1			
Charge Injection ^d	Q	CL = 1 nF, RGEN = 0 Ω, VGEN = 0 V	Room		10.4		pC	
Off-Isolation ^d	OIRR	RL = 50 Ω, CL = 5 pF, f = 1 MHz	Room		- 79		dB	
		RL = 50 Ω, CL = 5 pF, f = 10 MHz			- 59			
		RL = 50 Ω, CL = 5 pF, f = 240 MHz			- 28			
Crosstalk ^d	XTALK	RL = 50 Ω, CL = 5 pF, f = 1 MHz			- 109			
		RL = 50 Ω, CL = 5 pF, f = 10 MHz			- 99			
		RL = 50 Ω, CL = 5 pF, f = 240 MHz			- 48			
3 dB bandwidth ^d		RL = 50 Ω, CL = 5 pF	Room		720		MHz	
Channel to Channel skew ^d		RL = 50 Ω, CL = 5 pF	Room		25		ps	
Skew of Opposite Transitions of the Same Output ^d					20			
Total Jitter ^d					200			
Source Off Capacitance ^d	CS(off)			f = 1 MHz, VS = 0 V	Room			4.4
Drain Off Capacitance ^d	CD(off)	f = 1 MHz, VD = 0 V	Room		3.8			
Drain On Capacitance ^d	CD(on)	f = 1 MHz, VD = VS = 0 V	Room		10			
Control Pin Capacitance ^d	CIN	f = 1 MHz	Room		8.3			
Power Supply								
Power Supply Range	V+			2.3		4.3	V	
Power Supply Current	I+	VIN = 0 or V+	Full			1.0	μA	

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

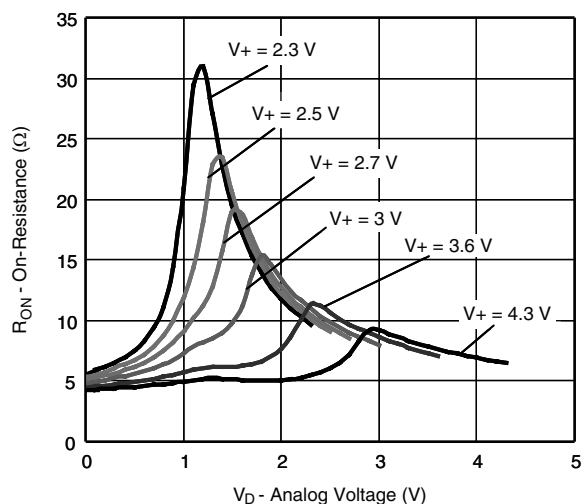
c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, not subjected to production test.

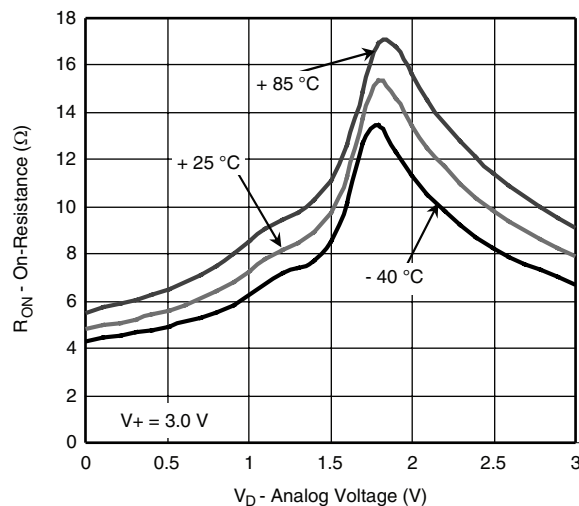
e. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

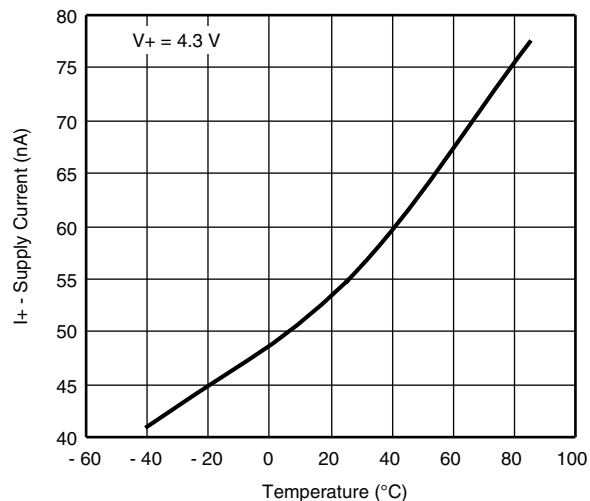
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



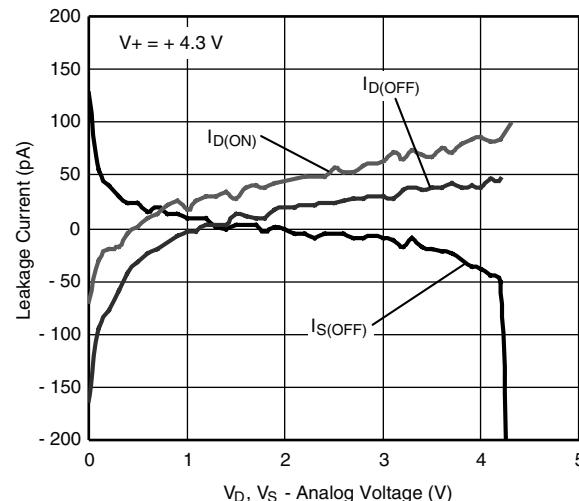
R_{ON} vs. V_D and Supply Voltage



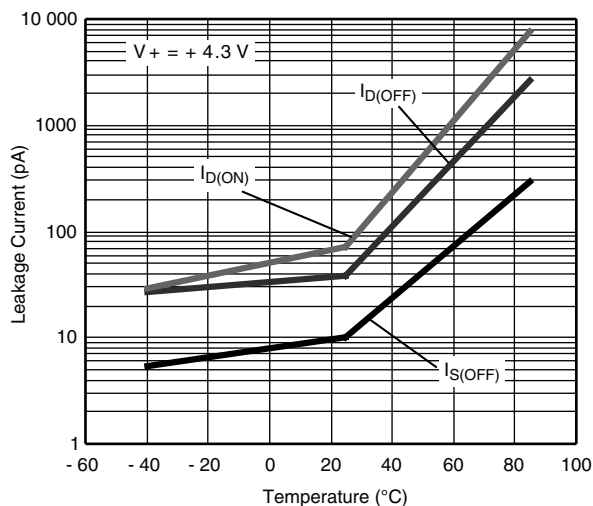
R_{ON} vs. V_D and Temperature



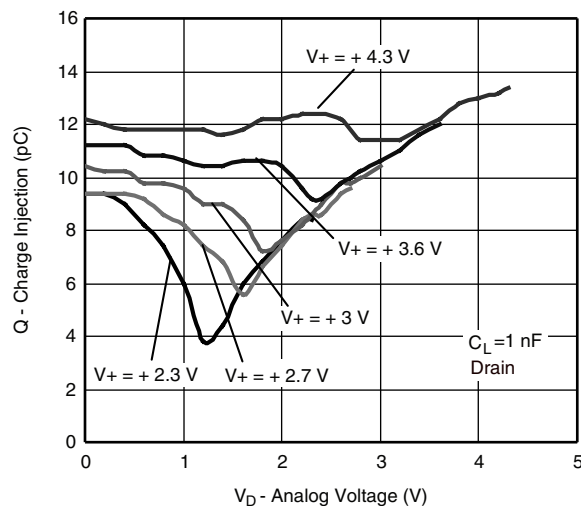
Supply Current vs. Temperature



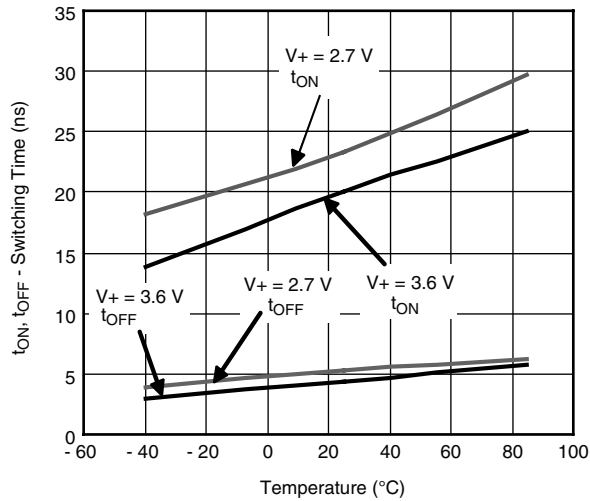
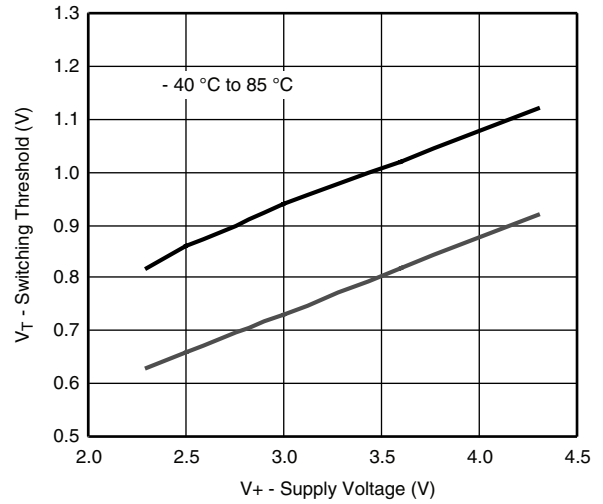
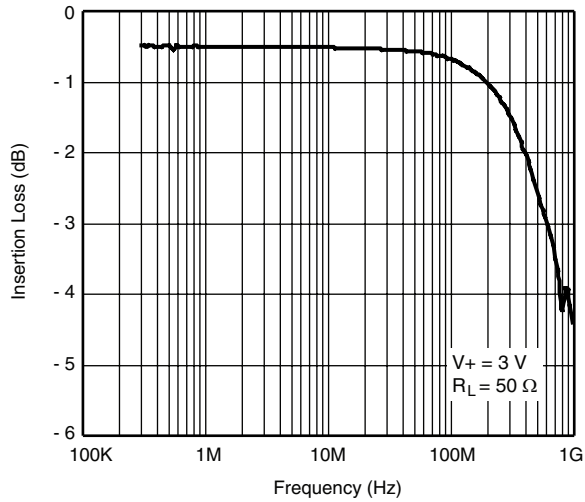
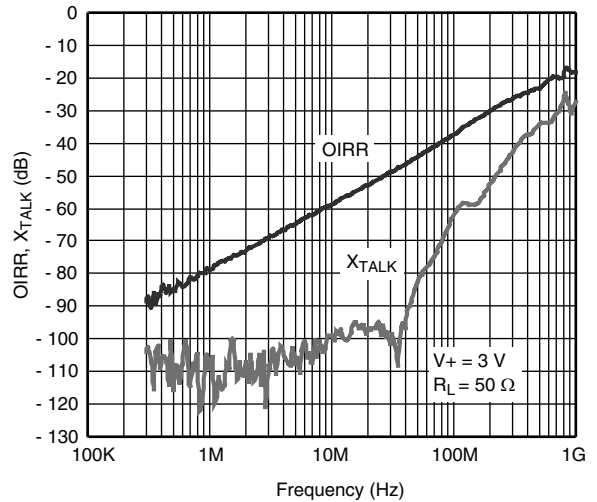
Leakage vs. Analog Voltage



Leakage Current vs. Temperature



Charge Injection vs. Analog Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Switching Time vs. Temperature

Switching Threshold vs. Supply Voltage

Insertion Loss vs. Frequency

Off-Isolation, Crosstalk vs. Frequency

TEST CIRCUITS

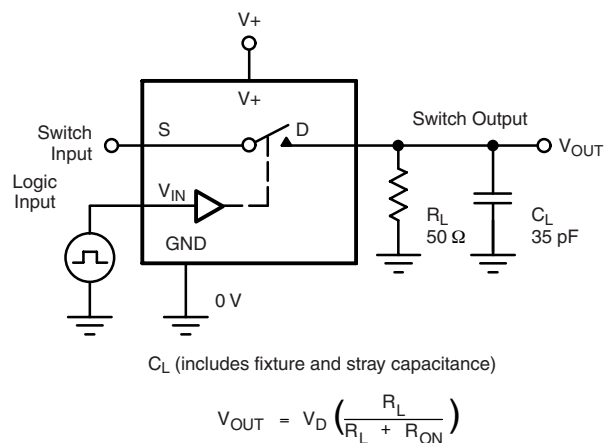


Figure 1. Switching Time

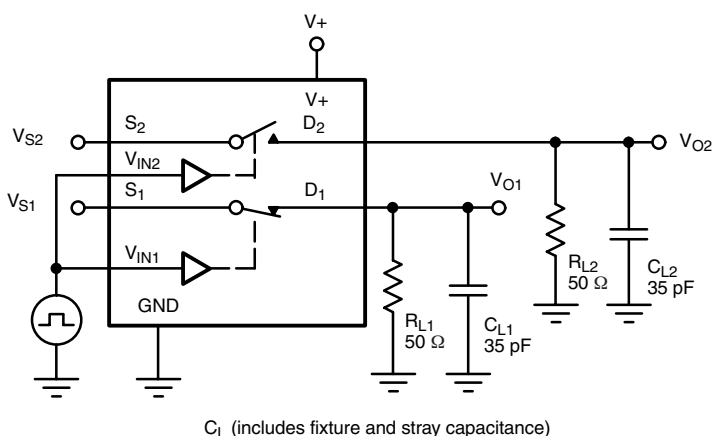


Figure 2. Break-Before-Make (DG2739)

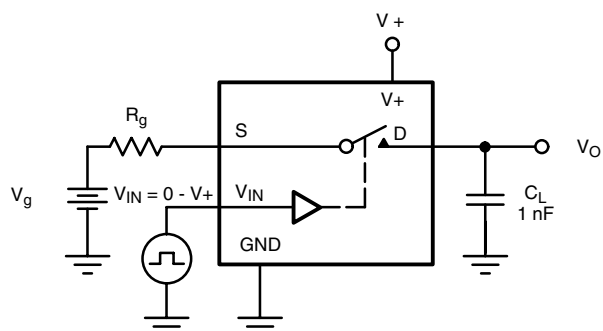


Figure 3. Charge Injection



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